DATA SHEET

EYP-DFB-0852-00050-1500-BFY02-0002

Revision 1.09

SINGLE FREQUENCY LASER DIODES
Distributed Feedback Laser

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General Product Information

Product	Application
Tunable 852 nm DFB Laser	Spectroscopy
with hermetic 14-Pin Butterfly Housing (RoHS compliant)	Metrology
including Monitor Diode, Thermoelectric Cooler and Thermistor	
with PM Fiber and angle-polished Connector (APC)	

Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Storage Temperature	T_S	°C	-40		85	Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.
Operational Temperature at Case	T_C	°C	-40		85	
Operational Temperature at Laser Chip	T_{LD}	°C	10		50	
Forward Current	I_F	mA			200	
Reverse Voltage	V_R	V			2	
Output Power	P_{opt}	mW			55	
TEC Current	I_{TEC}	A			1.8	
TEC Voltage	V_{TEC}	V			3.2	

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Operational Temperature at Case	T_{case}	°C	-20		65	
Operational Temperature at Laser Chip	T_{LD}	°C	15		45	measured by integrated Thermistor
Forward Current	I_F	mA			180	
Output Power	P_{opt}	mW	10		50	

Characteristics at T_{LD} = 25° at BOL

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Center Wavelength	λ_C	nm	851	852	853	see images on page 4
Linewidth (FWHM)	$\Delta\lambda$	MHz		2		see note 1)
Mode-hop free Tuning Range	$\Delta\lambda_{tune}$	pm		1500		see note 1)
Temperature Coefficient of Wavelength	$d\lambda / dT$	nm / K		0.06		
Current Coefficient of Wavelength	$d\lambda / dI$	nm / mA		0.003		
Sidemode Supression Ratio	SMSR	dB	30	45		P_{opt} = 50 mW

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Characteristics at T_{LD} = 25° at BOL cont'd

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Mode-hop free Temperature Range	T_{LD}	° C	15		40	Temperature at Laser Chip
Mode-hop free Power Range	P_{opt}	mW	10		50	
Laser Current @ P_{opt} = 50 mW	I_{LD}	mA			180	
Slope Efficiency	η	W / A	0.2	0.5	0.7	
Threshold Current	I_{th}	mA			70	
Polarization Extinction Ratio	PER	dB		20		P_{opt} = 50 mW

1) This variant allows wavelength tuning by temperature or current variation; in case of external backreflections small mode-hops of 100 MHz or less may appear; the use of a BFW01 or TOC03 package variants and effective optical isolation is recommended for spectroscopic application requiring absolutely mode-hop-free tuning.

Monitor Diode

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Monitor Detector Responsivity	I_{mon} / P_{opt}	µA/mW	1		20	U_R = 5 V

Thermoelectric Cooler

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Current	I_{TEC}	A		0.4		P_{opt} = 50 mW, ΔT = 20 K
Voltage	U_{TEC}	V		0.8		P_{opt} = 50 mW, ΔT = 20 K
Power Dissipation (total loss at case)	P_{loss}	W		0.5		P_{opt} = 50 mW, ΔT = 20 K
Temperature Difference	ΔT	K			50	P_{opt} = 50 mW, ΔT = |Tcase - TLD|

Thermistor (Standard NTC Type)

Parameter	Symbol	Unit	min	typ	max	Measurement Conditions / Comments
Resistance	R	kΩ		10		T_{LD} = 25° C
Beta Coefficient	β			3892		$R_1 / R_2 = e^{\beta (1/T_1 - 1/T_2)}$ at T_{LD} = 0° … 50° C
Steinhart & Hart Coefficient A	A			1.1293×10^{-3}		$1/T = A + B(\ln R) + C(\ln R)^3$
Steinhart & Hart Coefficient B	B			2.3410×10^{-4}		T: temperature in Kelvin
Steinhart & Hart Coefficient C	C			8.7755×10^{-8}		R: resistance at T in Ohm

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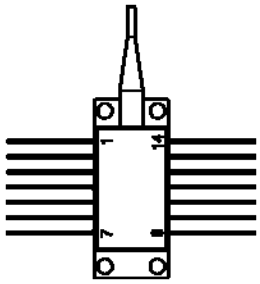
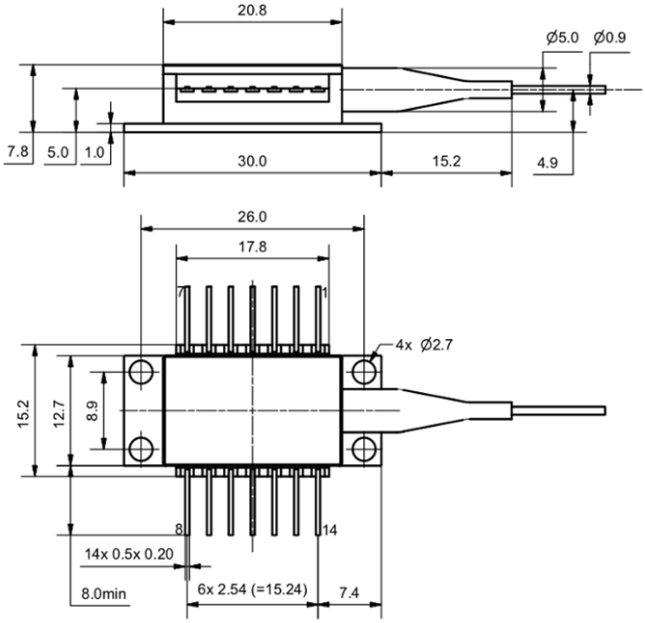
Pin Assignment

1	Thermoelectric Cooler (+)	14	Thermoelectric Cooler (-)
2	Thermistor	13	Case
3	Photodiode (Anode)	12	not connected
4	Photodiode (Cathode)	11	Laser Diode (Cathode)
5	Thermistor	10	Laser Diode (Anode)
6	not connected	9	not connected
7	not connected	8	not connected

All 14 pins are isolated from case.



Package Drawings



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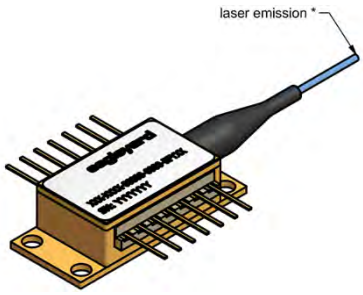
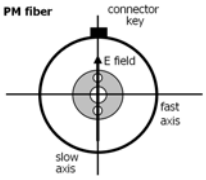


Fiber and Connector Type

PM Fiber	900 / 125 / 5.5 µm, UV/Polyester-elastomer Coating (l = 1 +/-0.1 m)
Connector	different variants available

Measurement Conditions / Comments



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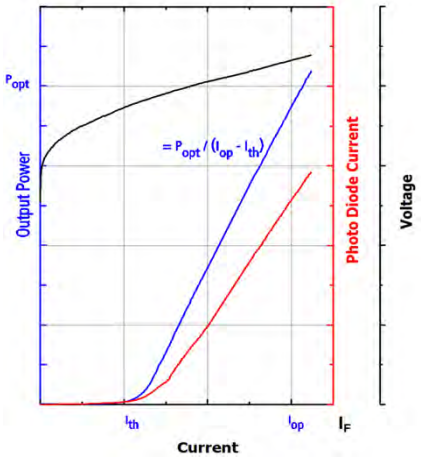
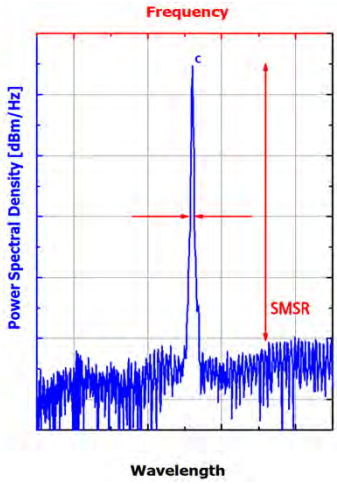
Typical Measurement Results

Output Power vs. Current



Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The DFB laser is sensitive against optical feedback, so an optical isolator may be required in order to avoid any disturbance of the emission spectrum. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

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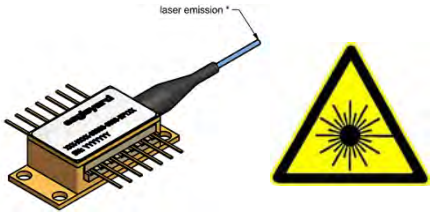

INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT
WAVELENGTH 852 nm
MAX. OUTPUT POWER 55 mW

IEC-60825-0

DANGER
INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE TO
DIRECT OR SCATTERED RADIATION
GaAs SEMICONDUCTOR LASER DIODE
55 mW MAX OUTPUT AT 852 nm
CLASS IV LASER PRODUCT

Complies with 21 CFR 1040.10 and 1040.40

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